



Y100900

1/5

特許協力条約に基づく国際出願願書

紙面による写し (注意 電子データが原本となります)

0	受理官庁記入欄	
0-1	国際出願番号	
0-2	国際出願日	
0-3	(受付印)	
0-4	様式 PCT/RO/101 この特許協力条約に基づく国際出願願書は、	
0-4-1	右記によって作成された。	JPO-PAS 0342
0-5	申立て 出願人は、この国際出願が特許協力条約に従って処理されることを請求する。	
0-6	出願人によって指定された受理官庁	日本国特許庁 (R0/JP)
0-7	出願人又は代理人の書類記号	Y100900
I	発明の名称	固体撮像素子、固体撮像装置及びその製造方法
II	出願人	
II-1	この欄に記載した者は	出願人である (applicant only)
II-2	右の指定国について出願人である。	米国を除く全ての指定国 (all designated States except US)
II-4ja	名称	日本ユニサンティスエレクトロニクス株式会社
II-4en	Name:	Unisant Electronics (Japan) Ltd.
II-5ja	あて名	1040033 日本国 東京都中央区新川 1-22-11 フジライト新川ビル 2F
II-5en	Address:	2F, Fujilight Shinkawa Bldg, 22-11, Shinkawa 1-c home, Chuo-ku, Tokyo 1040033 Japan
II-6	国籍 (国名)	日本国 JP
II-7	住所 (国名)	日本国 JP
II-11	出願人登録番号	506240584

Title of the invention:

SOLID-STATE IMAGE SENSOR, SOLID-STATE IMAGE SENSING DEVICE, AND METHOD OF PRODUCING THE SAME

特許協力条約に基づく国際出願願書

紙面による写し(注意 電子データが原本となります)

III-1	その他の出願人又は発明者	出願人及び発明者である (applicant and inventor) 米国のみ (US only) 舩岡 富士雄 MASUOKA Fujio 1040033 日本国 東京都中央区新川 1-22-11 フジライト新川ビル 2F 日本ユニサントイスエレクトロニクス株式会社内 c/o Unisantis Electronics (Japan) Ltd., 2F, Fuji light Shinkawa Bldg, 22-11, Shinkawa 1-chome, Chuo-ku, Tokyo 1040033 Japan
III-1-1	この欄に記載した者は	
III-1-2	右の指定国についての出願人である。	
III-1-4ja	氏名(姓名)	
III-1-4en	Name (LAST, First):	
III-1-5ja	あて名	
III-1-5en	Address:	
III-1-6	国籍(国名)	日本国 JP
III-1-7	住所(国名)	日本国 JP
III-2	その他の出願人又は発明者	出願人及び発明者である (applicant and inventor) 米国のみ (US only) 中村 広記 NAKAMURA Hiroki 1040033 日本国 東京都中央区新川 1-22-11 フジライト新川ビル 2F 日本ユニサントイスエレクトロニクス株式会社内 c/o Unisantis Electronics (Japan) Ltd., 2F, Fuji light Shinkawa Bldg, 22-11, Shinkawa 1-chome, Chuo-ku, Tokyo 1040033 Japan
III-2-1	この欄に記載した者は	
III-2-2	右の指定国についての出願人である。	
III-2-4ja	氏名(姓名)	
III-2-4en	Name (LAST, First):	
III-2-5ja	あて名	
III-2-5en	Address:	
III-2-6	国籍(国名)	日本国 JP
III-2-7	住所(国名)	日本国 JP

特許協力条約に基づく国際出願願書

紙面による写し(注意 電子データが原本となります)

IV-1	代理人又は共通の代表者、通知のあて名 下記の者は国際機関において右 記のごとく出願人のために行動する。	代理人 (agent)	
IV-1-1ja	氏名(姓名)	熊倉 禎男	
IV-1-1en	Name (LAST, First):	KUMAKURA Yoshio	
IV-1-2ja	あて名	1008355 日本国 東京都千代田区丸の内3丁目3番1号 新東京ビル 中村合同特許法律事務所	
IV-1-2en	Address:	NAKAMURA & PARTNERS, Shin-Tokyo Bldg., 3-1, Maru nouchi 3-chome, Chiyoda-ku, Tokyo 1008355 Japan	
IV-1-3	電話番号	03-3211-8741	
IV-1-4	ファクシミリ番号	03-3214-6358	
IV-1-6	代理人登録番号	100082005	
IV-2	その他の代理人	筆頭代理人と同じあて名を有する代理人 (additional agent(s) with the same address as first named agent)	
IV-2-1ja	氏名	大塚 文昭(100067013); 西島 孝喜(100086771); 須田 洋之(100109070); 谷口 信行(100151987)	
IV-2-1en	Name(s)	OHTSUKA Fumiaki (100067013); NISHIJIMA Takaki (100086771); SUDA Hiroyuki (100109070); TANIGUCHI Nobuyuki (100151987)	
V	国の指定		
V-1	この願書を用いてされた国際出願は、規則 4.9(a)に基づき、国際出願の時点で拘束さ れる全てのPCT締約国を指定し、取得しうる あらゆる種類の保護を求め、及び該当する 場合には広域と国内特許の両方を求める 国際出願となる。		
VI-1	優先権主張	なし (NONE)	
VII-1	特定された国際調査機関(ISA)	日本国特許庁 (ISA/JP)	
VIII	申立て	申立て数	
VIII-1	発明者の特定に関する申立て	-	
VIII-2	出願し及び特許を与えられる国際出 願日における出願人の資格に関する 申立て	-	
VIII-3	先の出願の優先権を主張する国際出 願日における出願人の資格に関する 申立て	-	
VIII-4	発明者である旨の申立て(米国を指定国と する場合)	-	
VIII-5	不利にならない開示又は新規性喪失 の例外に関する申立て	-	

特許協力条約に基づく国際出願願書

紙面による写し(注意 電子データが原本となります)

IX	照合欄	用紙の枚数	添付された電子データ
IX-1	願書(申立てを含む)	5	✓
IX-2	明細書	23	✓
IX-3	請求の範囲	5	✓
IX-4	要約	1	✓
IX-5	図面	47	✓
IX-7	合計	81	
	添付書類	添付	添付された電子データ
IX-8	手数料計算用紙	-	✓
IX-17	PCT-SAFE 電子出願	-	-
IX-19	要約書とともに提示する図の番号	2	
IX-20	国際出願の使用言語名	日本語	
X-1	出願人、代理人又は代表者の記名押印	/100082005/	
X-1-1	氏名(姓名)	熊倉 禎男	
X-1-2	署名者の氏名		
X-1-3	権限		
X-2	出願人、代理人又は代表者の記名押印	/100067013/	
X-2-1	氏名(姓名)	大塚 文昭	
X-2-2	署名者の氏名		
X-2-3	権限		
X-3	出願人、代理人又は代表者の記名押印	/100086771/	
X-3-1	氏名(姓名)	西島 孝喜	
X-3-2	署名者の氏名		
X-3-3	権限		
X-4	出願人、代理人又は代表者の記名押印	/100109070/	
X-4-1	氏名(姓名)	須田 洋之	
X-4-2	署名者の氏名		
X-4-3	権限		
X-5	出願人、代理人又は代表者の記名押印	/100151987/	
X-5-1	氏名(姓名)	谷口 信行	
X-5-2	署名者の氏名		
X-5-3	権限		

特許協力条約に基づく国際出願願書

紙面による写し (注意 電子データが原本となります)

受理官庁記入欄

10-1	国際出願として提出された書類 の実際の受理の日	
10-2	図面	
10-2-1	受理された	
10-2-2	不足図面がある	
10-3	国際出願として提出された書類 を補完する書類又は図面であつ てその後期間内に提出されたも のの実際の受理の日(訂正日)	
10-4	特許協力条約第11条(2)に基づ く必要な補完の期間内の受理の日	
10-5	出願人により特定された国際調査機関	ISA/JP
10-6	調査手数料未払いにつき、国際 調査機関に調査用写しを送付していない	

国際事務局記入欄

11-1	記録原本の受理の日	
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PCT手数料計算用紙(願書付属書)

紙面による写し(注意 電子データが原本となります)
 [この用紙は、国際出願の一部を構成せず、国際出願の用紙の枚数に算入しない]

0	受理官庁記入欄			
0-1	国際出願番号			
0-2	受理官庁の日付印			
0-4	様式 PCT/RO/101(付属書) このPCT手数料計算用紙は、 0-4-1 右記によって作成された。	JPO-PAS 0342		
0-9	出願人又は代理人の書類記号	Y100900		
2	出願人	日本ユニサンティスエレクトロニクス株式会社		
12	所定の手数料の計算	金額/係数	小計(JPY)	
12-1	送付手数料 T	⇒	13000	
12-2	調査手数料 S	⇒	97000	
12-3	国際出願手数料 (最初の30枚まで) i1	138200		
12-4	30枚を越える用紙の枚数	51		
12-5	用紙1枚の手数料 (X)	1500		
12-6	合計の手数料 i2	76500		
12-7	i1 + i2 = i	214700		
12-12	fully electronic filing fee reduction R	-29600		
12-13	国際出願手数料の合計 (i-R) I	⇒	185100	
12-17	納付するべき手数料の合計 (T+S+I+P)	⇒	295100	
12-19	支払方法	送付手数料: 予納口座引き落としの承認 調査手数料: 予納口座引き落としの承認 国際出願手数料: 銀行口座への振込み		
12-20	予納口座 受理官庁	日本国特許庁 (R0/JP)		
12-20-1	上記手数料合計額の請求に対する承認	✓		
12-21	予納口座番号	228497		
12-22	日付	2007年 12月 26日 (26.12.2007)		
12-23	記名押印			

DESCRIPTION

SOLID-STATE IMAGE SENSOR, SOLID-STATE IMAGE SENSING DEVICE, AND METHOD OF PRODUCING THE SAME

5

TECHNICAL FIELD

[0001]

The present invention relates to a solid-state image
sensor, a solid-state image sensing device, and a method
10 of producing the same, and in particular, to a CCD
solid-state image sensor, a CCD solid-state image sensing
device, and a method of producing the same.

BACKGROUND ART

15 [0002]

A conventional solid-state image sensor used in a
video camera or the like, in which light sensing elements
are arranged in matrix form, includes, between light
sensing element lines, a vertical charge coupled device
20 (Vertical CCD: Charge Coupled Device) for reading signal
charges generated by the light sensing element lines.

[0003]

A structure of the aforementioned conventional
solid-state image sensor will be described in the following
25 (refer to, for example, Patent Document 1). Fig. 1 is a
sectional view showing a unit pixel of the conventional
solid state-image sensor. A photodiode (PD) are composed

of an n-type photoelectric conversion region 13 which is formed in a p-type well region 12 formed on an n-type substrate 11 and functions as a charge storage layer, and a p⁺-type region 14 formed on the n-type photoelectric conversion region 13.

[0004]

An n-type CCD channel region 16 is formed in the p-type well region 12 as an n-type impurity region. There is provided a read channel formed by a p-type impurity region between the n-type CCD channel region 16 and the photodiode on the side of reading the signal charge to the n-type CCD channel region 16. The signal charge generated in the photodiode is read through the read channel after being temporarily stored in the n-type photoelectric conversion region 13.

[0005]

There is provided a p⁺-type isolation region 15 between the n-type CCD channel region 16 and other photodiodes. By the p⁺-type isolation region 15, the photodiodes and the n-type CCD channel region 16 are isolated, and respective n-type CCD channels 16 also are isolated not to touch with each other.

[0006]

A transfer electrode 18 is formed on a surface of the semiconductor substrate via a Si oxide film 17, which horizontally extends so as to pass through between the photodiodes. Incidentally, the signal charge generated

in the photodiode is read to the n-type CCD channel region 16 through a read channel below a transfer electrode to which a read signal is applied among the transfer electrodes 18.

5 [0007]

A metal shield film 20 is formed on the surface of the semiconductor substrate in which the transfer electrode 18 is formed. The metal shield film 20 includes a metal shield film opening 24 for every photodiode as a
10 light transmitting portion which transmits the light received by the p⁺-type region 14 acting as a light receiving portion.

[0008]

Patent Document 1; Japanese Unexamined Patent
15 Publication (Kokai) No. 2000-101056

DISCLOSURE OF THE INVENTION

PROBLEM TO BE SOLVED BY THE INVENTION

[0009]

20 As described above, in the conventional solid-state image sensors, the photodiode (PD), the read channel, n-type CCD channel region, and the p⁺-type isolation region are formed in a plane, and thus there has been a limitation in increasing a ratio of a surface area of the light
25 receiving portion (photodiode) to an area of one pixel. Therefore, it is an object to provide a CCD solid-state image sensor, in which an area of the read channel is

reduced, and the ratio of the surface area of the light receiving portion (photodiode) to the area of one pixel is increased.

5 MEANS FOR SOLVING THE PROBLEM

[0010]

A first aspect of the present invention is to provide a solid-state image sensor including: a first conductive type semiconductor layer; a first conductive type
10 pillar-shaped semiconductor layer formed on the first conductive type semiconductor layer; a second conductive type photoelectric conversion region formed on the top of the first conductive type pillar-shaped semiconductor layer, an electric charge amount of the photoelectric
15 conversion region being changed by light; and a high-concentrated impurity region of the first conductive type formed on a surface of the second conductive type photoelectric conversion region, the impurity region being spaced apart from a top end of the first conductive
20 type pillar-shaped semiconductor layer by a predetermined distance, wherein a transfer electrode is formed on the side of the first conductive type pillar-shaped semiconductor layer via a gate insulating film, a second conductive type CCD channel region is formed below the
25 transfer electrode, and a read channel is formed in a region between the second conductive type photoelectric conversion region and the second conductive type CCD

channel region.

[0011]

A second aspect of the present invention is to provides a solid-state image sensing device in which a plurality of solid-state image sensors are arranged in matrix form, the solid-state image sensor including: a first conductive type semiconductor layer; a first conductive type pillar-shaped semiconductor layer formed on the first conductive type semiconductor layer; a second conductive type photoelectric conversion region formed on the top of the first conductive type pillar-shaped semiconductor layer, an electric charge amount of the photoelectric conversion region being changed by light; and a high-concentrated impurity region of the first conductive type formed on a surface of the second conductive type photoelectric conversion region, the impurity region being spaced apart from a top end of the first conductive type pillar-shaped semiconductor layer by a predetermined distance, wherein a transfer electrode is formed on the side of the first conductive type pillar-shaped semiconductor layer via a gate insulating film, a second conductive type CCD channel region is formed below the transfer electrode, and a read channel is formed in a region between the second conductive type photoelectric conversion region and the second conductive type CCD channel region.

[0012]

Preferably, the second conductive type CCD channel region is composed of a second conductivity type impurity region extending in a column direction, at least in respective portions between adjacent columns of the first conductive type pillar-shaped semiconductor layers, and an isolation region composed of high-concentrated impurities of the first conductivity type is provided so that the second conductivity type CCD channel regions may not contact with each other.

10 [0013]

More preferably, a plurality of transfer electrodes including the transfer electrodes formed on the side of the first conductive type pillar-shaped semiconductor layer via the gate insulating film extend in a row direction, in respective portions between the adjacent rows of the first conductive type pillar-shaped semiconductor layers, and are arranged at a predetermined space so as to transfer a signal charge generated in the solid-state image sensor along the second conductive type CCD channel region.

20 [0014]

A third aspect of the present invention is to provide a solid-state image sensing device, wherein a solid-state image sensor includes a first conductive type semiconductor layer, a first conductive type pillar-shaped semiconductor layer formed on the first conductive type semiconductor layer, a second conductive type photoelectric conversion region formed on the top of

the first conductive type pillar-shaped semiconductor layer, an electric charge amount of the photoelectric conversion region being changed by light, and a high-concentrated impurity region of the first conductive type formed on a surface of the second conductive type photoelectric conversion region, the impurity region being spaced apart from a top end of the first conductive type pillar-shaped semiconductor layer by a predetermined distance, wherein a transfer electrode is formed on the side of the first conductive type pillar-shaped semiconductor layer via a gate insulating film, a second conductive type CCD channel region is formed below the transfer electrode, and a read channel is formed in a region between the second conductive type photoelectric conversion region and the second conductive type CCD channel region, and wherein a plurality of sets of the columns of solid-state image sensors, in which a first column of solid-state image sensors in which a plurality of solid-state image sensors are arranged in a first direction at a first space, and a second column of solid-state image sensors in which a plurality of solid-state image sensors are arranged in the first direction at the first space, and are displacedly arranged by a predetermined amount in the first direction with respect to the first column of solid-state image sensors are displacedly arranged at a second space are displacedly arranged by a predetermined amount in the first direction

at the second space.

[0015]

Preferably, the second conductive type CCD channel region is composed of a second conductive type impurity region which extends in the column direction passing through between respective pillar-shaped semiconductor layers of the adjacent columns of the first conductive type pillar-shaped semiconductor layers, at least in respective portions between the adjacent columns of the pillar-shaped semiconductor layers, and an isolation region composed of high-concentrated impurities of the first conductivity type is provided so that the second conductivity type CCD channel regions may not contact with each other.

15 [0016]

More preferably, the transfer electrodes extend in the row direction passing through between respective pillar-shaped semiconductor layers of the adjacent rows of the pillar-shaped semiconductor layers, in respective portions between adjacent rows of the pillar-shaped semiconductor layers, and are arranged at a predetermined space so as to transfer a signal charge generated in the solid-state image sensor along the second conductive type CCD channel region.

25 [0017]

A fourth aspect of the present invention is to provide a method of producing a solid-state image sensor, including

the steps of: forming a first conductive type semiconductor layer, a first conductive type pillar-shaped semiconductor layer on the first conductive type semiconductor layer, a second conductive type

5 photoelectric conversion region on the top of the first conductive type pillar-shaped semiconductor layer, and a high-concentrated impurity region of the first conductive type on a surface of the second conductive type photoelectric conversion region, the impurity region
10 being spaced apart from a top end of the first conductive type pillar-shaped semiconductor layer by a predetermined distance; forming a second conductive type CCD channel region on the surface of the first conductive type semiconductor layer; forming a gate insulating film on the
15 side of the first conductive type pillar-shaped semiconductor layer; and forming a transfer electrode on the side of the first conductive type pillar-shaped semiconductor layer via the gate insulating film, above the second conductive type CCD channel region.

20 [0018]

Preferably, the step of forming the first conductive type semiconductor layer, the first conductive type pillar-shaped semiconductor layer on the first conductive type semiconductor layer, the second conductive type
25 photoelectric conversion region on the top of the first conductive type pillar-shaped semiconductor layer, and the high-concentrated impurity region of the first

conductive type on the surface of the second conductive type photoelectric conversion region, the impurity region being spaced apart from the top end of the first conductive type pillar-shaped semiconductor layer by the

5 predetermined distance, further includes the steps of: forming a semiconductor layer of the first conductive type with a larger thickness than the first conductive type semiconductor layer; forming a semiconductor layer of the second conductive type on the semiconductor layer of the

10 first conductive type with the larger thickness than the first conductive type semiconductor layer; forming a semiconductor layer with high-concentrated impurities of the first conductive type on the second conductive type semiconductor layer; selectively etching the

15 semiconductor layer of the first conductive type with the larger thickness than the first conductive type semiconductor layer, the semiconductor layer of the second conductive type, and the semiconductor layer with high-concentrated impurities of the first conductivity

20 type to form the first conductive type semiconductor layer, the first conductive type pillar-shaped semiconductor layer on the first conductive type semiconductor layer, the second conductive type photoelectric conversion region on the top of the first conductive type

25 pillar-shaped semiconductor layer, and the high-concentrated impurity region of the first conductive type on the upper surface of the second conductive type

photoelectric conversion region; forming an oxide film on the surface of the first conductive type semiconductor layer, the side of the second conductive type photoelectric conversion region, and the side of the first conductive type pillar-shaped semiconductor layer; depositing a masking material on the side surface of the first conductive type pillar-shaped semiconductor layer, the mask material being used in forming the high-concentrated impurity region of the first conductive type on the side surface of the second conductive type photoelectric conversion region by ion implantation; and forming the high-concentrated impurity region of the first conductive type on the side surface of the second conductive type photoelectric conversion region by ion implantation.

[0019]

A fifth aspect of the present invention is to provide a method of producing a solid-state image sensing device, including the steps of: forming a first conductive type semiconductor layer, a plurality of first conductive type pillar-shaped semiconductor layers on the first conductive type semiconductor layer, a second conductive type photoelectric conversion region on the top of each of the plurality of first conductive type pillar-shaped semiconductor layers, and a high-concentrated impurity region of the first conductive type on the surface of the second conductive type photoelectric conversion region, the impurity region being spaced apart from the top end

of the first conductive type pillar-shaped semiconductor layers; forming a second conductive type CCD channel region on the surface of the first conductive type semiconductor layer; forming a gate insulating film on the sides of the
5 plurality of first conductive type pillar-shaped semiconductor layers; and forming a transfer electrode on the sides of the plurality of first conductive type pillar-shaped semiconductor layers via the gate insulating film, above the second conductive type CCD
10 channel region.

[0020]

Preferably, the step of forming the first conductive type semiconductor layer, the plurality of first conductive type pillar-shaped semiconductor layers on the
15 first conductive type semiconductor layer, the second conductive type photoelectric conversion region on the top of each of the plurality of first conductive type pillar-shaped semiconductor layers, and the high-concentrated impurity region of the first conductive
20 type on the surface of the second conductive type photoelectric conversion region, the impurity region being spaced apart from a top end of the first conductive type pillar-shaped semiconductor layer by a predetermined distance further includes the steps of forming a
25 semiconductor layer of the first conductive type with a larger thickness than the first conductive type semiconductor layer; forming a semiconductor layer of the

second conductive type on the semiconductor layer of the first conductive type with the larger thickness than the first conductive type semiconductor layer; forming a semiconductor layer with high-concentrated impurities of the first conductive type on the second conductive type semiconductor layer; selectively etching the semiconductor layer of the first conductive type with the larger thickness than the first conductive type semiconductor layer, the semiconductor layer of the second conductive type, and the semiconductor layer with high-concentrated impurities of the first conductivity type to form the first conductive type semiconductor layer, the plurality of first conductive type pillar-shaped semiconductor layers on the first conductive type semiconductor layer, the second conductive type photoelectric conversion region on the top of the plurality of first conductive type pillar-shaped semiconductor layers, and the high-concentrated impurity region of the first conductive type on the upper surface of the second conductive type photoelectric conversion region; forming an oxide film on the surface of the first conductive type semiconductor layer, the side of the second conductive type photoelectric conversion region, and the side of the first conductive type pillar-shaped semiconductor layer; depositing a masking material between the plurality of first conductive type pillar-shaped semiconductor layers, the mask material being used in forming the

high-concentrated impurity region of the first conductive type on the side surface of the second conductive type photoelectric conversion region by ion implantation; and forming the high-concentrated impurity region of the first
5 conductive type on the side surface of the second conductive type photoelectric conversion region by ion implantation.

[0021]

Preferably, the step of forming the second conductive
10 type CCD channel region on the surface of the first conductive type semiconductor layer is the steps of forming a second conductivity type impurity region on the surface of the first conductive type semiconductor layer between the plurality of first conductive type pillar-shaped
15 semiconductor layers, forming an isolation region composed of high-concentrated impurities of the first conductivity type in the second conductivity type impurity region, and forming a second conductive type CCD channel region which extends in the column direction at least in
20 respective portions between adjacent columns of the first conductive type pillar-shaped semiconductor layers, and is mutually-isolated.

[0022]

Preferably, the step of forming the second conductive
25 type CCD channel region on the surface of the first conductive type semiconductor layer, further includes the steps of: forming a nitride film on the sides of the

plurality of first conductive type pillar-shaped semiconductor layers and the sides of the second conductive type photoelectric conversion region; forming a second conductive type impurity region on the surface of the first conductive type semiconductor layer between the plurality of first conductive type pillar-shaped semiconductor layers; depositing a masking material for forming the isolation region which is composed of the high-concentrated impurities of the first conductivity type on the second conductivity type impurity region; and forming the isolation region which is composed of the high-concentrated impurities of the first conductivity type in the second conductivity type impurity region by ion implantation, whereby a second conductive type CCD channel region which extends in the column direction at least in respective portions between adjacent columns of the first conductive type pillar-shaped semiconductor layers, and is mutually-isolated is formed.

[0023]

More preferably, the step of forming the nitride film on the sides of the plurality of first conductive type pillar-shaped semiconductor layers and the side of the second conductive type photoelectric conversion region is a step of leaving the nitride film in a sidewall spacer shape on the sides of the plurality of first conductive type pillar-shaped semiconductor layers, the side of the second conductive type photoelectric conversion region,

and the side of the high-concentrated impurity region of the first conductive type on the surface of the second conductive type photoelectric conversion region, by forming the nitride film on the surface of a structure
5 formed at the previous step of this step to perform etch-back thereto.

EFFECT OF THE INVENTION

[0024]

10 The photo diode (PD), the read channel, the n type CCD channel region, and the p⁺-type isolation region are formed in a plain face, and thus there has been a limitation in increasing the ratio of the surface area of the light receiving (photo diode) to the area of one pixel, in the
15 conventional CCD solid-state image sensor, but according to the present invention, it is possible to provide the CCD solid-state image sensor, in which an occupation area of the read channel can be greatly reduced by arranging the read channel non-horizontally, and the ratio of the
20 surface area of the light receiving portion (photodiode) to the area of one pixel is increased.

BEST MODE(S) FOR CARRYING OUT THE INVENTION

[0025]

25 Hereinafter, embodiments of the present invention will be described in detail with reference to the accompanying drawings.

[0026]

Figs. 2 and 3 show a perspective view and a plan view of one CCD solid-state image sensor according to a first embodiment of the present invention, respectively. Fig. 4 is a cross-sectional view taken from line X_1-X_1' shown in Fig. 3, and Fig. 5 is a cross-sectional view taken from line Y_1-Y_1' shown in Fig. 3.

[0027]

A p-type well region 112 is formed on an n-type substrate 111, and a p-type pillar-shaped semiconductor layer 131 is further formed on the p-type well region 112. An n-type photoelectric conversion region 113 in which an amount of charge is changed by light is formed on the top of the p-type pillar-shaped semiconductor layer 131, and a p⁺-type region 114 is further formed on the surface of the n-type photoelectric conversion region 113, while being spaced apart from the top end of the p-type pillar-shaped semiconductor layer 131 by a predetermined distance. A light receiving portion (photodiode) 130 is formed of the p⁺-type region 114 and the n-type photoelectric conversion region 113. Transfer electrodes 118 and 119 are formed on the side of the p-type pillar-shaped semiconductor layer 131 via a gate insulating film 133. An n-type CCD channel region 116 is formed below the transfer electrodes 118 and 119. A read channel 132 is formed in a region between the n-type photoelectric conversion region 113 on the top of the

p-type pillar-shaped semiconductor layer and the n-type CCD channel region 116. Moreover, a p⁺-type isolation region 115 is formed below the transfer electrodes 118 and 119 for isolation. A metal shield film 120 is connected
5 to the p⁺-type region 114. An oxide film 121 is formed as an interlayer insulation film.

[0028]

When a read signal is applied to the transfer electrodes 118 or 119, a signal charge accumulated in the
10 photodiode 130 will be read into the n-type CCD channel region 116 through the read channel 132. Moreover, the read signal charge is transferred in the vertical (Y₁-Y₁') direction by the transfer electrodes 118 and 119.

[0029]

15 Next, a perspective view and a plan view of a part of a solid-state image sensing device which is the second embodiment of the present invention and in which a plurality of CCD solid-state image sensors of the first embodiment are arranged in matrix form are shown in Figs.
20 6 and 7, respectively.

[0030]

In Figs. 6 and 7, the solid-state image sensors having photodiodes (PDs) 147, 149, and 151 which have p⁺-type regions 153, 155, and 157, respectively, are arranged on
25 a semiconductor substrate, at a predetermined spacing (a vertical pixel pitch VP) and in the vertical (Y₂-Y₂') direction (column direction) (a first column of

solid-state image sensors). While being adjacent to respective solid-state image sensors of the first column of solid-state image sensors and at the same positions in the vertical direction, the solid-state image sensors
5 having photodiodes (PD) 148, 150, 152 respectively including p⁺-type regions 154, 156, 158 are arranged in the vertical direction at the same predetermined spacing (vertical pixel pitch VP) as that of the first column of solid-state image sensors (a second column of solid-state
10 image sensors). The first column of solid-state image sensors and the second column of solid-state image sensors are arranged at the same spacing (horizontal pixel pitch HP) as the vertical pixel pitch. As is understood, the solid-state image sensors having the photodiodes 147, 149,
15 151, 148, 150, and 152 are arranged in so-called matrix form.

[0031]

An n-type CCD channel region 160 for reading and vertically transferring the signal charges generated in
20 the photodiodes 147, 149, and 151 is provided between the p-type pillar-shaped semiconductor layer of the first column of solid-state image sensors and the p-type pillar-shaped semiconductor layer of the second column of solid-state image sensors which are adjacently arranged.
25 Similarly, in order to read and vertically transfer the signal charges generated in other photodiodes, the n-type CCD channel regions 159 and 161 are provided. The n-type

CCD channel region is vertically extended between the p-type pillar-shaped semiconductor layers arranged in matrix form. Moreover, p⁺-type isolation regions 162 and 163 are provided so that the n-type CCD channel regions
5 may be isolated not to contact with each other. Although the p⁺-type isolation regions 162 and 163 are provided along the axes of the first and second columns of solid-state image sensors and the outer edges of the p-type pillar-shaped semiconductor layers in the present
10 embodiment, p⁺-type isolation region should just be provided so that adjacent n-type CCD channel regions may not contact with each other, for example, the p⁺-type isolation regions 162 and 163 can also be displacedly arranged in an X₂ direction from the arrangement shown in
15 Fig. 7.

[0032]

Between the p-type pillar-shaped semiconductor layers of a first row of solid-state image sensors in which the solid-state image sensors having the photodiodes 151
20 and 152 are arranged in the horizontal (X₂-X₂') direction (row direction) and the p-type pillar-shaped semiconductor layers of a second row of solid-state image sensors in which the solid-state image sensors having the photodiodes 149 and 150 are arranged in the horizontal
25 direction, transfer electrodes 146, 145, and 144 for vertically transferring the signal charges read from the photodiodes into the n-type CCD channel regions 159, 160,

and 161 are provided. Moreover, between the p-type pillar-shaped semiconductor layers of the second row of solid-state image sensors in which the solid-state image sensors having the photodiodes 149 and 150 are arranged in the horizontal direction and the p-type pillar-shaped semiconductor layers of a third row of solid-state image sensors in which the solid-state image sensors having the photodiodes 147 and 148 are arranged in the horizontal direction, transfer electrodes 143, 142, and 141 are provided. When the read signal is applied to the transfer electrode 143, the signal charges accumulated in the photodiodes 149 and 150 will be read into the n-type CCD channel regions 160 and 161 through the read channel. The transfer electrode is horizontally extended between the p-type pillar-shaped semiconductor layers arranged in matrix form.

[0033]

Incidentally, the photodiode 147 is composed of the p⁺-type region 153 and the n-type photoelectric conversion region 166, while the photodiode 148 is composed of the p⁺-type region 154 and the n-type photoelectric conversion region 167.

[0034]

Fig. 8 is a cross-sectional view taken from line X₂-X₂' shown in Fig. 7, and Fig. 9 is a cross-sectional view taken from line Y₂-Y₂' in Fig. 7.

[0035]

The solid-state image sensor of the second row and the first column in Fig. 7 will be described. A p-type well region 165 is formed on an n-type substrate 164, and a p-type pillar-shaped semiconductor layer 181 is further
5 formed on the p-type well region 165. An n-type photoelectric conversion region 168 in which the amount of charge is changed by light is formed on the top of a p-type pillar-shaped semiconductor layer 181, and a p⁺-type region 155 is further formed on the surface of the
10 n-type photoelectric conversion region 168, while being spaced apart from the top end of the p-type pillar-shaped semiconductor layer 181 by a predetermined distance. The photodiode 149 is formed of the p⁺-type region 155 and the n-type photoelectric conversion region 168. Moreover,
15 the transfer electrodes 143 and 144 are formed on the side of the p-type pillar-shaped semiconductor layer via a gate insulating film 185. The n-type CCD channel region 160 is formed below the transfer electrodes 143 and 144. A read channel 182 is formed in a region between the n-type
20 photoelectric conversion region 168 on the top of the p-type pillar-shaped semiconductor layer 181 and the n-type CCD channel region 160.

[0036]

Subsequently, the solid-state image sensor of the
25 second row and the second column in Fig. 7 will be described. The p-type well region 165 is formed on the n-type substrate 164, and a p-type pillar-shaped semiconductor layer 183

is further formed on the p-type well region 165. An n-type photoelectric conversion region 169 in which the amount of charge is changed by light is formed on the top of the p-type pillar-shaped semiconductor layer 183, and a
5 p⁺-type region 156 is further formed on the surface of the n-type photoelectric conversion region 169, while being spaced apart from the top end of the p-type pillar-shaped semiconductor layer 183 by a predetermined distance. The light receiving portion (photodiode) 150 is formed of the
10 p⁺-type region 156 and the n-type photoelectric conversion region 169. Moreover, the transfer electrodes 143 and 144 are formed on the side of the p-type pillar-shaped semiconductor layer 183 via a gate insulating film 186. The n-type CCD channel region 161 is formed below the
15 transfer electrodes 143 and 144. A read channel 184 is formed in a region between the n-type photoelectric conversion region 169 on the top of the p-type pillar-shaped semiconductor layer 183 and the n-type CCD channel region 161.

20 [0037]

A metal shield film 170 is connected to the p⁺-type regions 155, 156, 153 and 157. An oxide film 180 is formed as an interlayer insulation film between respective components. Moreover, p⁺-type isolation regions 162 and
25 163 are provided so that the n-type CCD channel regions may be isolated not to contact with each other. Although the p⁺-type isolation regions 162 and 163 are provided

along the axes of the first and second columns of solid-state image sensors and the outer edges of the p-type pillar-shaped semiconductor layers in the present embodiment, p⁺-type isolation region should just be
5 provided so that adjacent n-type CCD channel regions may not contact with each other, for example, the p⁺-type isolation regions 162 and 163 can also be displacedly arranged in an X₂ direction from the arrangement shown in Fig. 7. Incidentally, the photodiode 151 is composed of
10 the p⁺-type region 157 and the n-type photoelectric conversion region 172.

[0038]

As described above, the transfer electrodes 141, 142, 143, 144, 145, and 146 extending in the row direction are
15 provided between the p-type pillar-shaped semiconductor layers of the adjacent rows of solid-state image sensors so as to pass through between the p-type pillar-shaped semiconductor layers of the adjacent rows of solid-state image sensor, and they are arranged spaced apart from each
20 other by a predetermined distance. The transfer electrodes 141, 143, 144, and 146 adjacent to the p-type pillar-shaped semiconductor layers are formed on the side of the p-type pillar-shaped semiconductor layers via the gate oxide film. The transfer electrodes 141, 142, 143,
25 144, 145, and 146 constitute a vertical charge transfer device (VCCD) for vertically transferring the signal charges generated in the photodiodes along with the n-type

CCD channel regions. The VCCD is driven in three phases ($\phi 1$ - $\phi 3$), and the signal charges generated in the photodiodes are vertically transferred by the three transfer electrodes driven with different phases with respect to each photodiode. Although the VCCD is driven in three phases in the present embodiment, it will be clear to those skilled in the art that the VCCD can also have the configuration driven by any appropriate number of phases.

10 [0039]

Although the solid-state image sensing device in which the CCD solid-state image sensors are arranged in matrix form has been shown in the second embodiment, the CCD solid-state image sensors may be arranged in honeycomb form as shown in Figs. 10, 11, 12, and 13. Accordingly, as the third embodiment of the present invention, the solid-state image sensing device in which the CCD solid-state image sensors of the first embodiment are arranged in honeycomb form will be described. A perspective view and a plan view of a part of the solid-state image sensing device in which the CCD solid-state image sensors are arranged in honeycomb form are shown in Figs. 10 and 11, respectively.

[0040]

25 In Figs. 10 and 11, the solid-state image sensors having photodiodes (PDs) 236 and 231 respectively including p^+ -type regions 228 and 223 are arranged on the

semiconductor substrate, at a predetermined spacing (a vertical pixel pitch VP) and in the vertical (Y_3-Y_3') direction (column direction) (the first column of solid-state image sensors). While being spaced apart from the first column of solid-state image sensors by one half of the same spacing (horizontal pixel pitch HP) as the vertical pixel pitch, the solid-state image sensor having photodiodes 234 and 239 respectively including p⁺-type regions 226 and 221 are arranged in the vertical direction at the same predetermined spacing as that of the first column of solid-state image sensors and they are displacedly arranged by one half of the vertical pixel pitch VP in the vertical direction with respect to the first column of solid-state image sensors (the second column of solid-state image sensors). Furthermore, while being spaced apart from the second column of solid-state image sensors by one half of the same spacing (horizontal pixel pitch HP) as the vertical pixel pitch, the solid-state image sensor having photodiodes 237 and 232 respectively including p⁺-type regions 229 and 224 are arranged in the vertical direction at the same predetermined spacing as that of the first column of solid-state image sensors and they are displacedly arranged by one half of the vertical pixel pitch VP in the vertical direction with respect to the second column of solid-state image sensors (a third column of solid-state image sensors). Similarly, while being spaced apart from the third column of solid-state

image sensors by one half of the same spacing (horizontal pixel pitch HP) as the vertical pixel pitch, the solid-state image sensor having photodiodes 235 and 240 respectively including p⁺-type regions 227 and 222 are
5 arranged in the vertical direction at the same spacing as that of the first column of solid-state image sensors, and they are displacedly arranged by one half of the vertical pixel pitch VP in the vertical direction with respect to the third column of solid-state image sensors (a fourth
10 column of solid-state image sensors); and while being spaced apart from the fourth column of solid-state image sensors by one half of the same spacing (horizontal pixel pitch HP) as the vertical pixel pitch, the solid-state image sensor having photodiodes 238 and 233 respectively
15 including p⁺-type regions 230 and 225 are arranged in the vertical direction at the same spacing as that of the first column of solid-state image sensors, and they are displacedly arranged by one half of the vertical pixel pitch VP in the vertical direction with respect to the
20 fourth column of solid-state image sensors (a fifth column of solid-state image sensors). In other words, the solid-state image sensors having the photodiodes 236, 231, 234, 239, 237, 232, 235, 240, 238, and 233 are arranged in so-called honeycomb form.

25 [0041]

Between the p-type pillar-shaped semiconductor layer of the first column of solid-state image sensors and the

p-type pillar-shaped semiconductor layers of the second column of solid-state image sensors which are adjacently arranged, the n-type CCD channel region 207 which reads and vertically transfers the signal charges generated in the photodiodes 236 and 231 is provided. Similarly, between the p-type pillar-shaped semiconductor layer of the second column of solid-state image sensors, and the p-type pillar-shaped semiconductor layer of the third column of solid-state image sensors, between the p-type pillar-shaped semiconductor layer of the third column of solid-state image sensors, and the p-type pillar-shaped semiconductor layer of the fourth column of solid-state image sensors, and between the p-type pillar-shaped semiconductor layer of the fourth column of solid-state image sensors, and the p-type pillar-shaped semiconductor layer of the fifth column of solid-state image sensors, an n-type CCD channel region 208 which reads and vertically transfers the signal charges generated in the photodiodes 234 and 239, an n-type CCD channel region 209 which reads and vertically transfers the signal charges generated in the photodiodes 237 and 232, and an n-type CCD channel region 210 which reads and vertically transfers the signal charges generated in the photodiodes 235 and 240 are provided, respectively. These n-type CCD channel regions are extended in the vertical direction while snaking through between the p-type pillar-shaped semiconductor layers arranged in honeycomb form. Moreover, p⁺-type

isolation regions 213, 214, 215, and 216 are provided so that the n-type CCD channel regions may be isolated not to contact with each other. Although the p⁺-type isolation regions 213, 214, 215, and 216 are provided along the axes
5 of the first through fifth columns of solid-state image sensors and the outer edges of the p-type pillar-shaped semiconductor layers in the present embodiment, the p⁺-type isolation region should just be provided so that adjacent n-type CCD channel regions may not contact with
10 each other, for example, the p⁺-type isolation regions 213, 214, 215, and 216 can also be displacedly arranged in the X₃ direction from the arrangement shown in Fig. 11.

[0042]

Between the p-type pillar-shaped semiconductor
15 layers of the first row of solid-state image sensors in which the solid-state image sensors having the photodiodes 236, 237, and 238 are arranged in the horizontal (X₃-X₃') direction (in the row direction), and the p-type pillar-shaped semiconductor layers of the second row of
20 solid-state image sensors in which the solid-state image sensors having the photodiodes 234 and 235 are arranged in the horizontal direction, transfer electrodes 206 and 205 are provided. Similarly, between the p-type pillar-shaped semiconductor layers of the second row of
25 solid-state image sensor in which the solid-state image sensors having the photodiodes 234 and 235 are arranged in the horizontal direction, and the p-type pillar-shaped

semiconductor layers of the third row of solid-state image sensors in which the solid-state image sensors having the photodiodes 231, 232, and 233 are arranged in the horizontal direction, and between the p-type

5 pillar-shaped semiconductor layers of the third row of solid-state image sensors in which the solid-state image sensors having the photodiodes 231, 232, and 233 are arranged in the horizontal direction, and the p-type pillar-shaped semiconductor layers of the fourth row of
10 solid-state image sensors in which the solid-state image sensors having the photodiodes 239 and 240 are arranged in the horizontal direction, transfer electrodes 204, 203 and the transfer electrodes 202, 201 are provided, respectively. These transfer electrodes are extended in
15 the horizontal direction while snaking through between the p-type pillar-shaped semiconductor layers arranged in honeycomb form.

[0043]

Incidentally, the photodiode 239 is composed of the
20 p⁺-type region 221 and the n-type photoelectric conversion region 217, and the photodiode 240 is composed of the p⁺-type region 222 and the n-type photoelectric conversion region 218.

[0044]

25 Fig. 12 is a cross-sectional view taken from line X₃-X₃' in Fig. 11, while Fig. 13 is a cross-sectional view taken from line Y₃-Y₃' in Fig. 11.

[0045]

The solid-state image sensor of the second row and the first column in Fig. 11 will be described. A p-type well region 212 is formed on an n-type substrate 211, and
5 a p-type pillar-shaped semiconductor layer 251 is further formed on the p-type well region 212. An n-type photoelectric conversion region 242 in which the amount of charge is changed by light is formed on the top of a p-type pillar-shaped semiconductor layer 251, and the
10 p⁺-type region 226 is further formed on the surface of the n-type photoelectric conversion region 242, while being spaced apart from the top end of the p-type pillar-shaped semiconductor layer 251 by a predetermined distance. Moreover, the transfer electrodes 204 and 205 are formed
15 on the side of the p-type pillar-shaped semiconductor layer 251 via a gate insulating film 255. The n-type CCD channel region 208 is formed below the transfer electrodes 204 and 205. A read channel 252 is formed in a region between the n-type photoelectric conversion region 242 on the top of
20 the p-type pillar-shaped semiconductor layer 251 and the n-type CCD channel region 208.

[0046]

Subsequently, the solid-state image sensor of the second row and the fourth column in Fig. 11 will be
25 described. The p-type well region 212 is formed on the n-type substrate 211, and a p-type pillar-shaped semiconductor layer 253 is further formed on the p-type

well region 212. An n-type photoelectric conversion region 243 in which the amount of charge is changed by light is formed on the top of the p-type pillar-shaped semiconductor layer 253, and the p⁺-type region 227 is
5 further formed on the surface of the n-type photoelectric conversion region 243, while being spaced apart from the top end of the p-type pillar-shaped semiconductor layer by a predetermined distance. Moreover, the transfer electrodes 204 and 205 are formed on the side of the p-type
10 pillar-shaped semiconductor layer 253 via a gate insulating film 256. The n-type CCD channel region 210 is formed below the transfer electrodes 204 and 205. A read channel 254 is formed in a region between the n-type photoelectric conversion region 243 on the top of the
15 p-type pillar-shaped semiconductor layer 253 and the n-type CCD channel region 210.

[0047]

Moreover, p⁺-type isolation regions 213, 214, 215, and 216 are provided so that the n-type CCD channel regions
20 may be isolated not to contact with each other. Although the p⁺-type isolation regions 213, 214, 215, and 216 are provided along the axes of the first through fifth columns of solid-state image sensor and the outer edges of the p-type pillar-shaped semiconductor layers in the present
25 embodiment, the p⁺-type isolation region should just be provided so that adjacent n-type CCD channel regions may not contact with each other, for example, the p⁺-type

isolation regions 213, 214, 215, and 216 can also be displacedly arranged in an X_3 direction from the arrangement shown in Fig. 11.

[0048]

5 As described above, the transfer electrodes 201, 202, 203, 204, 205, and 206 extending in the row direction are provided between the p-type pillar-shaped semiconductor layers of the adjacent rows of solid-state image sensors so as to pass through between the p-type pillar-shaped
10 semiconductor layers of the adjacent rows of solid-state image sensors. The transfer electrodes 201, 202, 203, 204, 205, and 206 are formed on the sides of the p-type pillar-shaped semiconductor layers via the gate oxide film, and are arranged spaced apart from each other by a
15 predetermined distance. The transfer electrodes 201, 202, 203, 204, 205, and 206 constitute a vertical charge transfer device (VCCD) for vertically transferring the signal charges generated in the photodiodes along with the n-type CCD channel regions. The VCCD is driven in four
20 phases (ϕ_1 - ϕ_4), and the signal charges generated in the photodiodes are vertically transferred by the four transfer electrodes driven with different phases with respect to each photodiode. Although the VCCD is driven in four phases in the present embodiment, it will be clear
25 to those skilled in the art that the VCCD can also have the configuration driven by any appropriate number of phases.

[0049]

The surfaces of the transfer electrodes 201, 202, 203, 204, 205, and 206 are covered with an oxide film (planarized film) 250, and a metal shield film 241 is formed on the oxide film. The metal shield film 241 has a circle-like opening portion for every photodiode as a light transmission portion for transmitting light received by the p⁺-type region acting as a light receiving portion.

[0050]

Note herein that, although it is not shown in the drawing, a color filter, a microlens, and the like are formed on the above metal shield film via a protective film or the planarized film in a manner similar to that of a usual CCD image sensor.

[0051]

Next, an example of a manufacturing process for forming the solid-state image sensor and the solid-state image sensing device according to the embodiment of the present invention will be described with reference to Figs.

14 through 30.

[0052]

In Figs. 14 through 30, drawing symbols (a) and (b) correspond to the X₂-X₂' cross-section and the Y₂-Y₂' cross-section of Fig. 7, respectively.

[0053]

The p-type well region 165 is formed on the silicon n-type substrate 164, and the n-type region 301 is formed

on the top of the p-type well region 165, and then the p⁺-type region 302 is formed (Figs. 14(a) and 14(b)).

[0054]

Next, an oxide film is deposited and etching is performed to form oxide film masks 303, 304, 305, and 306 (Figs. 15(a) and 15(b)).

[0055]

Silicon is etched to form the pillar-shaped semiconductors 181, 183, 307, and 308 (Figs. 16(a) and 16(b)).

[0056]

An oxide film 309 is formed for ion channeling prevention upon ion implantation (Figs. 17(a) and 17(b)).

[0057]

A polysilicon 310 is deposited so as to be used as a mask upon ion implantation and is planarized, and etchback is performed thereto (Figs. 18(a) and 18(b)). Other materials such as a photoresist or the like may also be used as a mask material.

[0058]

Ion implantation is performed to form the p⁺-type regions 155, 156, 153, and 157 (Figs. 19(a) and 19(b)).

[0059]

The polysilicon is etched and removed (Figs. 20(a) and 20(b)).

[0060]

A nitride film is deposited and etchback is performed

to then leave it in the form of sidewall spacers 311, 312, 313, and 314 on the pillar-shaped semiconductor sidewall so as to use it as a mask upon ion implantation (Figs. 21(a) and 21(b)).

5 [0061]

An n-type region 315 which will be an n-type CCD channel region later is formed (Figs. 22(a) and 22(b)).

[0062]

Photoresists 316, 317, and 318 which are mask
10 materials for forming the p⁺-type isolation regions are formed (Figs. 23(a) and 23(b)).

[0063]

Ion implantation is performed to form the p⁺-type isolation regions 162 and 163 (Figs. 24(a) and 24(b)).

15 [0064]

The photoresist, the nitride film, and the oxide film are removed in this order (Figs. 25(a) and 25(b)).

[0065]

Gate oxidation is performed to form a gate oxide film
20 319, and a polysilicon 320 is deposited and planarized, and etchback is performed thereto (Figs. 26(a) and 26(b)).

[0066]

Photoresists 321, 322, 323, 324, 325, and 326 for forming the transfer electrodes are formed (Figs. 27(a)
25 and 27(b)).

[0067]

The polysilicon is etched to form the transfer

electrodes 141, 142, 143, 144, 145, and 146 (Figs. 28(a) and 28(b)).

[0068]

5 The photoresist is removed, and an oxide film 180 is deposited and planarized, and etchback is performed thereto (Figs. 29(a) and 29(b)).

[0069]

The metal shield film 170 is deposited and planarized, and etchback is performed thereto (Figs. 30(a) and 30(b)).

10 [0070]

Although the pillar-shaped semiconductor layer is formed by etching the semiconductor layer in the above embodiment, the pillar-shaped semiconductor layer may also be formed by another method, for example, an epitaxial
15 growth.

[0071]

The pillar-shaped semiconductor layers of the solid-state image sensor and the solid-state image sensing device are formed on the p-type well region formed on the
20 n-type substrate in the above embodiment, but it is not limited to this, and it may also be formed on the silicon layer on an insulating film formed on the substrate (for example, on an SOI substrate), for example.

[0072]

25 Moreover, although the n-type photoelectric conversion region formed on the top of the p-type pillar-shaped semiconductor layer is pillar-shaped with

the same diameter as that of the p-type pillar-shaped semiconductor layer in the above embodiment, it may be formed into any appropriate shapes other than that.

[0073]

5 Moreover, the transfer electrode can be composed of an electrode material generally used in a semiconductor process or a solid state device in the above embodiments. For example, it may include a low resistivity polysilicon, tungsten (W), molybdenum (Mo), a tungsten silicide (WSi),
10 a molybdenum silicide (MoSi), a titanium silicide (TiSi), a tantalum silicide (TaSi), and a copper silicide (CuSi). Moreover, the transfer electrode may be formed by stacking these electrode materials in layers without including the insulating film.

15 [0074]

 Additionally, the metal shield film may be formed of, for example, a metal film such as aluminum (Al), chromium (Cr), tungsten (W), titanium (Ti), molybdenum (Mo), or the like, an alloy film composed of two or more kinds of these
20 metals, a multilayered metal film in which two or more kinds selected from a group including the above metal films and the above alloy films are combined.

[0075]

 As described above, although the present invention
25 has been described in terms of several embodiments for the purposes of illustration, the present invention is not limited thereto and it will be clear to those skilled in

the art that various changes and modifications can be made to the embodiments and the details without departing from the scope and spirit of the present invention.

5 BRIEF DESCRIPTION OF THE DRAWINGS

[0076]

Fig. 1 illustrates a cross-sectional view of a unit pixel of a conventional solid-state image sensor;

Fig. 2 illustrates a perspective view of one CCD
10 solid-state image sensor in accordance with the present invention;

Fig. 3 illustrates a plan view of one CCD solid-state image sensor in accordance with the present invention;

Fig. 4 illustrates a cross-sectional view taken from
15 line X_1-X_1' shown in Fig. 3;

Fig. 5 illustrates a cross-sectional view taken from line Y_1-Y_1' shown in Fig. 3;

Fig. 6 illustrates a perspective view of CCD solid-state image sensors arranged in matrix form;

20 Fig. 7 illustrates a plan view of CCD solid-state image sensors arranged in matrix form;

Fig. 8 illustrates a cross-sectional view taken from line X_2-X_2' shown in Fig. 7;

Fig. 9 illustrates a cross-sectional view taken from
25 line Y_2-Y_2' shown in Fig. 7;

Fig. 10 illustrates a perspective view of CCD solid-state image sensors arranged in honeycomb form;

Fig. 11 illustrates a plan view of CCD solid-state image sensors arranged in honeycomb form;

Fig. 12 illustrates a cross-sectional view taken from line X_3-X_3' shown in Fig. 11;

5 Fig. 13 illustrates a cross-sectional view taken from line Y_3-Y_3' shown in Fig. 11;

Fig. 14(a) illustrates a cross-sectional process view taken from X_2-X_2' , showing an example of production of the solid-state image sensor in accordance with the
10 present invention;

Fig. 14(b) illustrates a cross-sectional process view taken from Y_2-Y_2' , showing the example of production of the solid-state image sensor in accordance with the present invention;

15 Fig. 15(a) illustrates a cross-sectional process view taken from X_2-X_2' , showing the example of production of the solid-state image sensor in accordance with the present invention;

Fig. 15(b) illustrates a cross-sectional process
20 view taken from Y_2-Y_2' , showing the example of production of the solid-state image sensor in accordance with the present invention;

Fig. 16(a) illustrates a cross-sectional process view taken from X_2-X_2' , showing the example of production
25 of the solid-state image sensor in accordance with the present invention;

Fig. 16(b) illustrates a cross-sectional process

view taken from Y_2-Y_2' , showing the example of production of the solid-state image sensor in accordance with the present invention;

Fig. 17(a) illustrates a cross-sectional process
5 view taken from X_2-X_2' , showing the example of production of the solid-state image sensor in accordance with the present invention;

Fig. 17(b) illustrates a cross-sectional process
view taken from Y_2-Y_2' , showing the example of production
10 of the solid-state image sensor in accordance with the present invention;

Fig. 18(a) illustrates a cross-sectional process
view taken from X_2-X_2' , showing the example of production of the solid-state image sensor in accordance with the
15 present invention;

Fig. 18(b) illustrates a cross-sectional process
view taken from Y_2-Y_2' , showing the example of production of the solid-state image sensor in accordance with the present invention;

20 Fig. 19(a) illustrates a cross-sectional process
view taken from X_2-X_2' , showing the example of production of the solid-state image sensor in accordance with the present invention;

Fig. 19(b) illustrates a cross-sectional process
25 view taken from Y_2-Y_2' , showing the example of production of the solid-state image sensor in accordance with the present invention;

Fig. 20(a) illustrates a cross-sectional process view taken from X_2-X_2' , showing the example of production of the solid-state image sensor in accordance with the present invention;

5 Fig. 20(b) illustrates a cross-sectional process view taken from Y_2-Y_2' , showing the example of production of the solid-state image sensor in accordance with the present invention;

10 Fig. 21(a) illustrates a cross-sectional process view taken from X_2-X_2' , showing the example of production of the solid-state image sensor in accordance with the present invention;

15 Fig. 21(b) illustrates a cross-sectional process view taken from Y_2-Y_2' , showing the example of production of the solid-state image sensor in accordance with the present invention;

20 Fig. 22(a) illustrates a cross-sectional process view taken from X_2-X_2' , showing the example of production of the solid-state image sensor in accordance with the present invention;

 Fig. 22(b) illustrates a cross-sectional process view taken from Y_2-Y_2' , showing the example of production of the solid-state image sensor in accordance with the present invention;

25 Fig. 23(a) illustrates a cross-sectional process view taken from X_2-X_2' , showing the example of production of the solid-state image sensor in accordance with the

present invention;

Fig. 23(b) illustrates a cross-sectional process view taken from Y_2-Y_2' , showing the example of production of the solid-state image sensor in accordance with the
5 present invention;

Fig. 24(a) illustrates a cross-sectional process view taken from X_2-X_2' , showing the example of production of the solid-state image sensor in accordance with the present invention;

10 Fig. 24(b) illustrates a cross-sectional process view taken from Y_2-Y_2' , showing the example of production of the solid-state image sensor in accordance with the present invention;

Fig. 25(a) illustrates a cross-sectional process
15 view taken from X_2-X_2' , showing the example of production of the solid-state image sensor in accordance with the present invention;

Fig. 25(b) illustrates a cross-sectional process view taken from Y_2-Y_2' , showing the example of production
20 of the solid-state image sensor in accordance with the present invention;

Fig. 26(a) illustrates a cross-sectional process view taken from X_2-X_2' , showing the example of production of the solid-state image sensor in accordance with the
25 present invention;

Fig. 26(b) illustrates a cross-sectional process view taken from Y_2-Y_2' , showing the example of production

of the solid-state image sensor in accordance with the present invention;

Fig. 27(a) illustrates a cross-sectional process view taken from X_2-X_2' , showing the example of production
5 of the solid-state image sensor in accordance with the present invention;

Fig. 27(b) illustrates a cross-sectional process view taken from Y_2-Y_2' , showing the example of production of the solid-state image sensor in accordance with the
10 present invention;

Fig. 28(a) illustrates a cross-sectional process view taken from X_2-X_2' , showing the example of production of the solid-state image sensor in accordance with the present invention;

15 Fig. 28(b) illustrates a cross-sectional process view taken from Y_2-Y_2' , showing the example of production of the solid-state image sensor in accordance with the present invention;

Fig. 29(a) illustrates a cross-sectional process
20 view taken from X_2-X_2' , showing the example of production of the solid-state image sensor in accordance with the present invention;

Fig. 29(b) illustrates a cross-sectional process view taken from Y_2-Y_2' , showing the example of production
25 of the solid-state image sensor in accordance with the present invention;

Fig. 30(a) illustrates a cross-sectional process

view taken from X_2-X_2' , showing the example of production of the solid-state image sensor in accordance with the present invention; and

Fig. 30(b) illustrates a cross-sectional process
5 view taken from Y_2-Y_2' , showing the example of production of the solid-state image sensor in accordance with the present invention.

EXPLANATIONS OF LETTERS OR NUMERALS

10 [0077]

11: n-type substrate

12: p-type well region

13: n-type photoelectric conversion region

14: p-type region

15 15: p^+ -type isolation region

16: n-type CCD channel region

17: Si oxide film

18: Transfer electrode

20: Metal shield film

20 24: Metal shield film opening

111: n-type substrate

112: p-type well region

113: n-type photoelectric conversion region

114: p^+ -type region

25 116: n-type CCD channel region

115: p^+ -type isolation region

118: Transfer electrode

119: Transfer electrode
 120: Metal shield film
 121: Oxide film
 130: Light receiving portion (photodiode)
 5 131: Pillar-shaped semiconductor layer
 132: Read channel
 133: Gate insulating film
 141: Transfer electrode
 142: Transfer electrode
 10 143: Transfer electrode
 144: Transfer electrode
 145: Transfer electrode
 146: Transfer electrode
 147: Photodiode (PD)
 15 148: Photodiode (PD)
 149: Photodiode (PD)
 150: Photodiode (PD)
 151: Photodiode (PD)
 152: Photodiode (PD)
 20 153: p⁺-type region
 154: p⁺-type region
 155: p⁺-type region
 156: p⁺-type region
 157: p⁺-type region
 25 158: p⁺-type region
 159: n-type CCD channel region
 160: n-type CCD channel region

161: n-type CCD channel region
 162: p⁺-type isolation region
 163: p⁺-type isolation region
 164: n-type substrate
 5 165: p-type well region
 166: n-type photoelectric conversion region
 167: n-type photoelectric conversion region
 168: n-type photoelectric conversion region
 169: n-type photoelectric conversion region
 10 170: Metal shield film
 172: n-type photoelectric conversion region
 180: Oxide film
 181: Pillar-shaped semiconductor layer
 182: Read channel
 15 183: Pillar-shaped semiconductor layer
 184: Read channel
 185: Gate insulating film
 186: Gate insulating film
 201: Transfer electrode
 20 202: Transfer electrode
 203: Transfer electrode
 204: Transfer electrode
 205: Transfer electrode
 206: Transfer electrode
 25 207: n-type CCD channel region
 208: n-type CCD channel region
 209: n-type CCD channel region

210: n-type CCD channel region
 211: n-type substrate
 212: p-type well region
 213: p⁺-type isolation region
 5 214: p⁺-type isolation region
 215: p⁺-type isolation region
 216: p⁺-type isolation region
 217: n-type photoelectric conversion region
 218: n-type photoelectric conversion region
 10 221: p⁺-type region
 222: p⁺-type region
 223: p⁺-type region
 224: p⁺-type region
 225: p⁺-type region
 15 226: p⁺-type region
 227: p⁺-type region
 228: p⁺-type region
 229: p⁺-type region
 230: p⁺-type region
 20 231: Photodiode (PD)
 232: Photodiode (PD)
 233: Photodiode (PD)
 234: Photodiode (PD)
 235: Photodiode (PD)
 25 236: Photodiode (PD)
 237: Photodiode (PD)
 238: Photodiode (PD)

239: Photodiode (PD)
 240: Photodiode (PD)
 241: Metal shield film
 242: n-type photoelectric conversion region
 5 243: n-type photoelectric conversion region
 250: Oxide film
 251: Pillar-shaped semiconductor layer
 252: Read channel
 253: Pillar-shaped semiconductor layer
 10 254: Read channel
 255: Gate insulating film
 256: Gate insulating film
 301: n-type region
 302: p⁺-type region
 15 303: Oxide film mask
 304: Oxide film mask
 305: Oxide film mask
 306: Oxide film mask
 307: Pillar-shaped semiconductor
 20 308: Pillar-shaped semiconductor
 309: Oxide film
 310: Polysilicon
 311: Sidewall spacer
 312: Sidewall spacer
 25 313: Sidewall spacer
 314: Sidewall spacer
 315: n-type region

	316: Photoresist
	317: Photoresist
	318: Photoresist
	319: Gate oxide film
5	320: Polysilicon
	321: Photoresist
	322: Photoresist
	323: Photoresist
	324: Photoresist
10	325: Photoresist
	326: Photoresist

CLAIMS

1. A solid-state image sensor, comprising:

a first conductive type semiconductor layer;

5 a first conductive type pillar-shaped semiconductor layer formed on the first conductive type semiconductor layer;

a second conductive type photoelectric conversion region formed on the top of the first conductive type pillar-shaped semiconductor layer, an electric charge
10 amount of the photoelectric conversion region being changed by light; and

a high-concentrated impurity region of the first conductive type formed on a surface of the second conductive type photoelectric conversion region, the
15 impurity region being spaced apart from a top end of the first conductive type pillar-shaped semiconductor layer by a predetermined distance, wherein

a transfer electrode is formed on sides of the first conductive type pillar-shaped semiconductor layer via a
20 gate insulating film,

a second conductive type CCD channel region is formed below the transfer electrode, and

a read channel is formed in a region between the second conductive type photoelectric conversion region and the
25 second conductive type CCD channel region.

2. A solid-state image sensing device, wherein a

plurality of solid-state image sensors according to claim 1 are arranged in matrix form.

3. The solid-state image sensing device according to
5 claim 2, wherein the second conductive type CCD channel region is composed of a second conductive type impurity region extending in a column direction at least in respective portions between adjacent columns of the first conductive type pillar-shaped semiconductor layers, and
10 an isolation region composed of high concentration impurities of the first conductive type is provided so that the second conductive type CCD channel regions may not contact with each other.

15 4. The solid-state image sensing device according to claim 3, wherein a plurality of transfer electrodes including the transfer electrodes formed on the side of the first conductive type pillar-shaped semiconductor layer via the gate insulating film extend in a row direction,
20 in respective portions between the adjacent rows of the first conductive type pillar-shaped semiconductor layers, and are arranged at a predetermined space so as to transfer a signal charge generated in the solid-state image sensor along the second conductive type CCD channel region.

25

5. A solid-state image sensing device, wherein a plurality of sets of the columns of solid-state image

sensors, in which a first column of solid-state image sensors in which a plurality of solid-state image sensors according to claim 1 are arranged in a first direction at a first space, and a second column of solid-state image sensors in which a plurality of solid-state image sensors according to claim 1 are arranged in the first direction at the first space and are displacedly arranged by a predetermined amount in the first direction with respect to the first column of solid-state image sensors are displacedly arranged at a second space are displacedly arranged by a predetermined amount in the first direction at the second space.

6. The solid-state image sensing device according to claim 5, wherein the second conductive type CCD channel region is composed of a second conductive type impurity region which extends in the column direction passing through between respective pillar-shaped semiconductor layers of the adjacent columns of the first conductive type pillar-shaped semiconductor layers, at least in respective portions between the adjacent columns of the pillar-shaped semiconductor layers, and an isolation region composed of high concentration impurities of the first conductive type is provided so that the second conductive type CCD channel regions may not contact with each other.

7. The solid-state image sensing device according to claim 6, wherein the transfer electrodes extend in the row direction passing through between respective pillar-shaped semiconductor layers of the adjacent rows of the pillar-shaped semiconductor layers, in respective portions between adjacent rows of the pillar-shaped semiconductor layers, and are arranged at a predetermined space so as to transfer a signal charge generated in the solid-state image sensor along the second conductive type CCD channel region.

8. A method of producing a solid-state image sensor, comprising the steps of:

forming a first conductive type semiconductor layer, a first conductive type pillar-shaped semiconductor layer on the first conductive type semiconductor layer, a second conductive type photoelectric conversion region on the top of the first conductive type pillar-shaped semiconductor layer, and a high-concentrated impurity region of the first conductive type on a surface of the second conductive type photoelectric conversion region, the impurity region being spaced apart from a top end of the first conductive type pillar-shaped semiconductor layer by a predetermined distance;

forming a second conductive type CCD channel region on a surface of the first conductive type semiconductor layer;

forming a gate insulating film on the side of the first conductive type pillar-shaped semiconductor layer; and

forming a transfer electrode on the side of the first conductive type pillar-shaped semiconductor layer via the gate insulating film, above the second conductive type CCD channel region.

9. The method of producing the solid-state image sensor according to claim 8, wherein the step of forming the first conductive type semiconductor layer, the first conductive type pillar-shaped semiconductor layer on the first conductive type semiconductor layer, the second conductive type photoelectric conversion region on the top of the first conductive type pillar-shaped semiconductor layer, and the high-concentrated impurity region of the first conductive type on a surface of the second conductive type photoelectric conversion region, the impurity region being spaced apart from a top end of the first conductive type pillar-shaped semiconductor layer by the predetermined distance further includes:

forming a semiconductor layer of the first conductive type with a larger thickness than the first conductive type semiconductor layer;

forming a semiconductor layer of the second conductive type on the semiconductor layer of the first conductive type with the larger thickness than the first conductive type semiconductor layer;

forming a semiconductor layer with high-concentrated impurities of the first conductive type on the second conductive type semiconductor layer;

5 selectively etching the semiconductor layer of the first conductive type with the larger thickness than the first conductive type semiconductor layer, the semiconductor layer of the second conductive type, and the semiconductor layer with high-concentrated impurities of the first conductivity type to form the first conductive
10 type semiconductor layer, the first conductive type pillar-shaped semiconductor layer on the first conductive type semiconductor layer, the second conductive type photoelectric conversion region on the top of the first conductive type pillar-shaped semiconductor layer, and
15 the high-concentrated impurity region of the first conductive type on the upper surface of the second conductive type photoelectric conversion region;

forming an oxide film on the surface of the first conductive type semiconductor layer, the side of the second
20 conductive type photoelectric conversion region, and the side of the first conductive type pillar-shaped semiconductor layer;

depositing a masking material on the side of the first conductive type pillar-shaped semiconductor layer, the
25 mask material being used in forming the high-concentrated impurity region of the first conductive type on the side surface of the second conductive type photoelectric

conversion region by ion implantation; and

forming the high-concentrated impurity region of the first conductive type on the side surface of the second conductive type photoelectric conversion region by ion
5 implantation.

10. A method of producing a solid-state image sensing device, comprising the steps of:

forming a first conductive type semiconductor layer,
10 a plurality of first conductive type pillar-shaped semiconductor layers on the first conductive type semiconductor layer, a second conductive type photoelectric conversion region on the top of each of the plurality of first conductive type pillar-shaped
15 semiconductor layers, and a high-concentrated impurity region of the first conductive type on the surface of the second conductive type photoelectric conversion region, the impurity region being spaced apart from the top end of the first conductive type pillar-shaped semiconductor
20 layers;

forming a second conductive type CCD channel region on the surface of the first conductive type semiconductor layer;

forming a gate insulating film on the sides of the
25 plurality of first conductive type pillar-shaped semiconductor layers; and

forming a plurality of transfer electrodes above the

second conductive type CCD channel region, the transfer electrodes including at least transfer electrodes formed on the sides of the plurality of first conductive type pillar-shaped semiconductor layers via the gate
5 insulating films.

11. The method of producing the solid-state image sensing device according to claim 10, wherein the step of forming the first conductive type semiconductor layer, the
10 plurality of first conductive type pillar-shaped semiconductor layers on the first conductive type semiconductor layer, the second conductive type photoelectric conversion region on the top of each of the plurality of first conductive type pillar-shaped
15 semiconductor layers, and the high-concentrated impurity region of the first conductive type on the surface of the second conductive type photoelectric conversion region, the impurity region being spaced apart from the top end of the first conductive type pillar-shaped semiconductor
20 layer by the predetermined distance, further includes:

forming a semiconductor layer of the first conductive type with a larger thickness than the first conductive type semiconductor layer;

forming a semiconductor layer of the second
25 conductive type on the semiconductor layer of the first conductive type with a larger thickness than the first conductive type semiconductor layer;

forming a semiconductor layer with high-concentrated impurities of the first conductive type on the second conductive type semiconductor layer;

selectively etching the semiconductor layer of the
5 first conductive type thicker than the first conductive type semiconductor layer, the semiconductor layer of the second conductive type, and the semiconductor layer with high-concentrated impurities of the first conductivity type to form the first conductive type semiconductor layer,
10 a plurality of first conductive type pillar-shaped semiconductor layers on the first conductive type semiconductor layer, a second conductive type photoelectric conversion region on the top of the plurality of first conductive type pillar-shaped semiconductor
15 layers, and a high-concentrated impurity region of the first conductive type on the upper surface of the second conductive type photoelectric conversion region;

forming an oxide film on the surface of the first conductive type semiconductor layer, the side of the second
20 conductive type photoelectric conversion region, and the side of the first conductive type pillar-shaped semiconductor layer;

depositing a masking material between the plurality of first conductive type pillar-shaped semiconductor
25 layers, the mask material being used in forming the high-concentrated impurity region of the first conductive type on the side surface of the second conductive type

photoelectric conversion region by ion implantation; and
forming the high-concentrated impurity region of the
first conductive type on the side surface of the second
conductive type photoelectric conversion region by ion
5 implantation.

12. The method of producing the solid-state image sensing
device according to claim 10 or 11, wherein the step of
forming the second conductive type CCD channel region on
10 the surface of the first conductive type semiconductor
layer is the steps of forming a second conductivity type
impurity region on the surface of the first conductive type
semiconductor layer between the plurality of first
conductive type pillar-shaped semiconductor layers,
15 forming an isolation region composed of high-concentrated
impurities of the first conductivity type in the second
conductivity type impurity region, and forming a second
conductive type CCD channel region which extends in the
column direction at least in respective portions between
20 adjacent columns of the first conductive type
pillar-shaped semiconductor layers, and is
mutually-isolated.

13. A method of producing the solid-state image sensing
25 device according to claim 10 or 11, wherein the step of
forming the second conductive type CCD channel region on
the surface of the first conductive type semiconductor

layer, further includes the steps of:

forming a nitride film on the sides of the plurality of first conductive type pillar-shaped semiconductor layers and the sides of the second conductive type photoelectric conversion region;

forming a second conductive type impurity region on the surface of the first conductive type semiconductor layer between the plurality of first conductive type pillar-shaped semiconductor layers;

depositing a masking material for forming the isolation region which is composed of the high-concentrated impurities of the first conductivity type on the second conductivity type impurity region; and

forming the isolation region which is composed of the high-concentrated impurities of the first conductivity type in the second conductivity type impurity region by ion implantation, whereby a second conductive type CCD channel region which extends in the column direction at least in respective portions between adjacent columns of the first conductive type pillar-shaped semiconductor layers, and is mutually-isolated is formed.

14. A method of producing the solid-state image sensing device according to claim 13, wherein the step of forming the nitride film on the sides of the plurality of first conductive type pillar-shaped semiconductor layers and the sides of the second conductive type photoelectric

conversion regions is a step of leaving the nitride film in a sidewall spacer shape on the sides of the plurality of first conductive type pillar-shaped semiconductor layers, the side of the second conductive type photoelectric conversion region, and the side of the high-concentrated impurity region of the first conductive type on the surface of the second conductive type photoelectric conversion region, by forming the nitride film on the surface of a structure formed at the previous step of this step to perform etch-back thereto.